

Silicon PNP Power Transistor

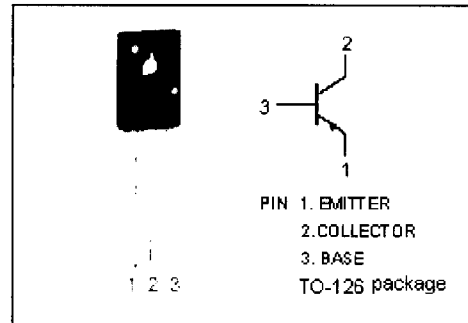
2SA1507

DESCRIPTION

- High Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = -160V$ (Min)
- Large Current Capacity
- Complement to Type 2SC3902

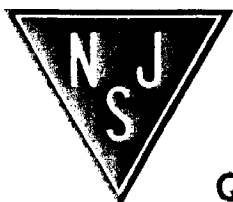
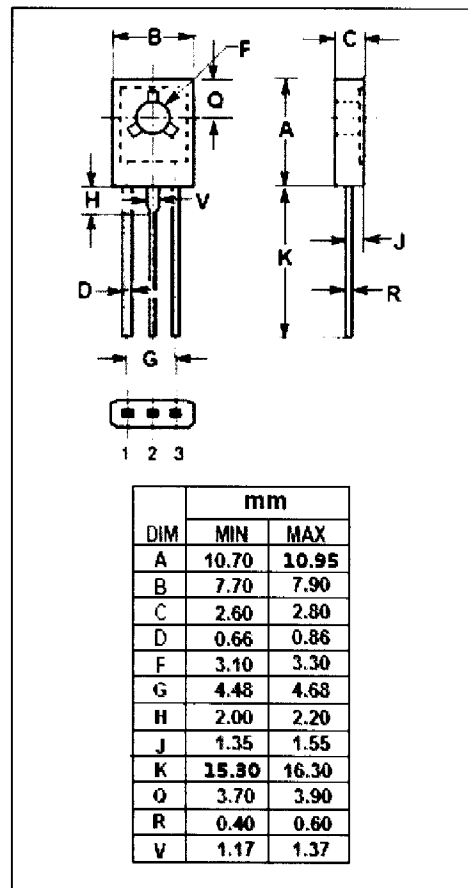
APPLICATIONS

- Designed for use in color TV audio output, converters and inverters.



ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-180	V
V_{CEO}	Collector-Emitter Voltage	-160	V
V_{EBO}	Emitter-Base Voltage	-6.0	V
I_C	Collector Current-Continuous	-1.5	A
I_{CM}	Collector Current-Peak	-2.5	A
P_C	Collector Power Dissipation @ $T_a=25^\circ C$	1.5	W
	Total Power Dissipation @ $T_c=25^\circ C$	10	
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C



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Quality Semi-Conductors

Silicon PNP Power Transistor

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ELECTRICAL CHARACTERISTICS

$T_C=25^\circ\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -10\mu\text{A}; I_E = 0$	180			V
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -1\text{mA}; R_{BE} = \infty$	160			V
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = -10\mu\text{A}; I_C = 0$	6			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -500\text{mA}; I_B = -50\text{mA}$			-0.5	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = -500\text{mA}; I_B = -50\text{mA}$			-1.2	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = -120\text{V}; I_E = 0$			-0.1	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = -4\text{V}; I_C = 0$			-0.1	μA
h_{FE-1}	DC Current Gain	$I_C = -100\text{mA}; V_{CE} = -5\text{V}$	100		400	
h_{FE-2}	DC Current Gain	$I_C = -10\text{mA}; V_{CE} = -5\text{V}$	90			
f_T	Current-Gain—Bandwidth Product	$I_C = -50\text{mA}; V_{CE} = -10\text{V}$		120		MHz
C_{OB}	Output Capacitance	$I_E = 0; V_{CB} = -10\text{V}; f = 1.0\text{MHz}$		22		pF

Switching Times

t_{on}	Turn-on Time	$I_C = -0.7\text{A}, R_L = 14.3\Omega,$ $I_{B1} = -I_{B2} = -70\text{mA}, V_{CC} = -100\text{V};$ $P_W = 20\mu\text{s}; \text{Duty Cycle} \leq 1\%$		0.04		μs
t_{stg}	Storage Time			0.7		μs
t_f	Fall Time			0.04		μs

◆ h_{FE-1} Classifications

R	S	T
100-200	140-280	200-400